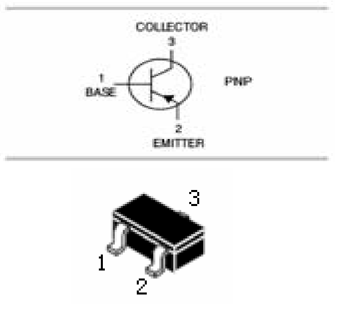
Silicon PNP Transistor **2SA2081**

FEATURES

- Low frequency amplifier

Lead-free



SOT-523

APPLICATIONS

- Epitaxial planar type.
- PNP silicon transistor.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA2081	CC/CD	SOT-523

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Limits**	**Unit**
V_{CBO}	collector-base voltage	-55	V
V_{CEO}	collector-emitter voltage	-55	V
V_{EBO}	emitter-base voltage	-5	V
I_C	collector current	-100	mA
P_d	Power dissipation	150	mW
T_{stg}	storage temperature range	-55 to +150	°C
T_j	junction temperature	150	°C

Silicon PNP Transistor 2SA2081

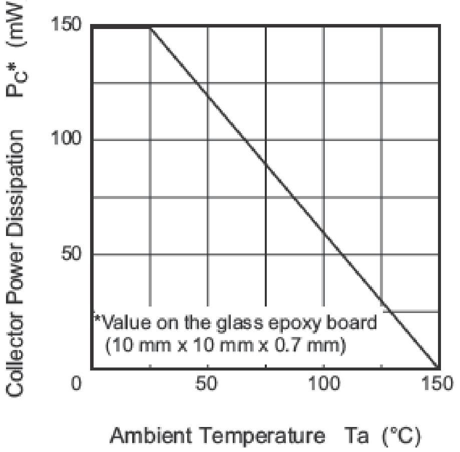
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

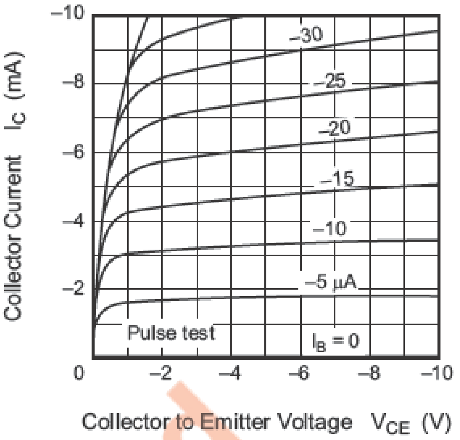
SYMBOL	PARAMETER	CONDITIONS	MIN.	Typ.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakown voltage	I_C=-10μA,I_E=0	-55			V
$V_{(BR)CEO}$	Collector- emitter breakown voltage	I_C=-1mA,I_B=0	-55			V
$V_{(BR)BEO}$	Emitter-base breakown voltage	I_E=-10μA,I_C=0	-5			V
I_{CBO}	Collector cut-off current	I_E=0,V_{CB}=-30V			-0.5	μA
I_{EBO}	Emitter cut-off current	I_C=0,V_{EB}=-2V			-0.5	μA
h_{FE}	DC current gain	V_{CE}=-12V,I_C=-2mA	160		500	
$V_{CE(sat)}$	collector-emitter saturation voltage	I_C=-10mA,I_B=-1mA			-0.5	V
V_{BE}	Base to emitter voltage	V_{CE}=-12V,I_C=-2mA			-0.75	V

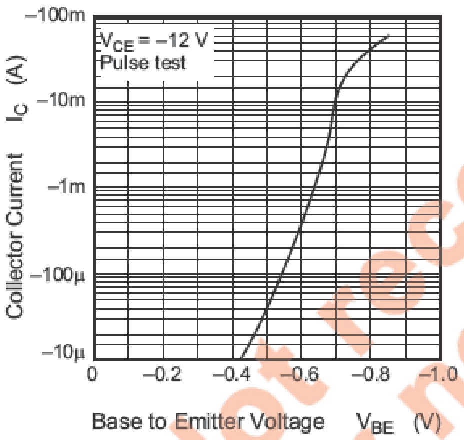
CLASSIFICATION OF h_{FE}

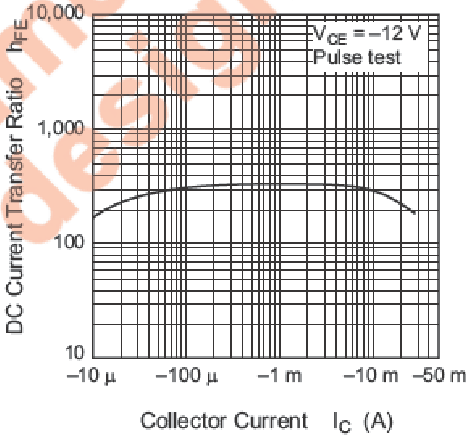
Rang	160-320	250-500
Marking	CC	CD

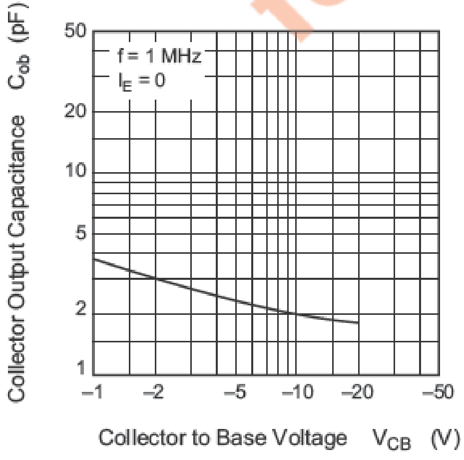
TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

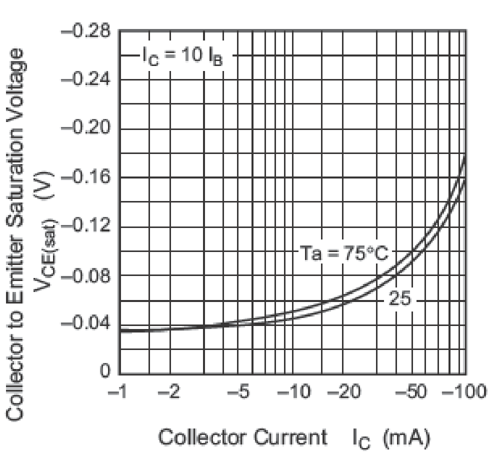

Maximum Collector Dissipation Curve


Typical Output Characteristics


Typical Transfer Characteristics

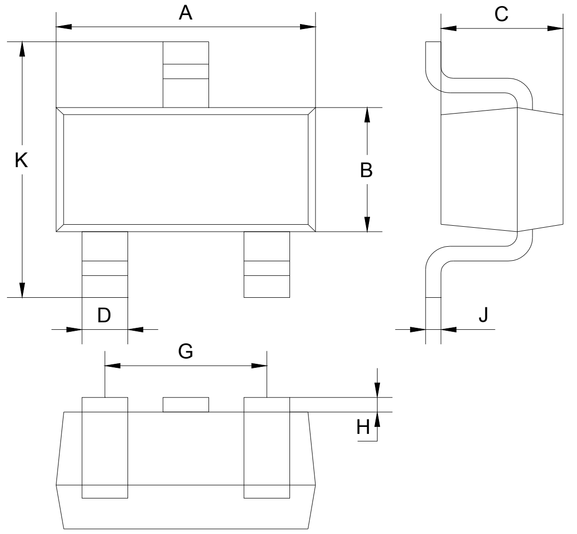

DC Current Transfer Ratio vs. Collector Current


Collector Output Capacitance vs. Collector to Base Voltage


Collector to Emitter Saturation Voltage vs. Collector Current

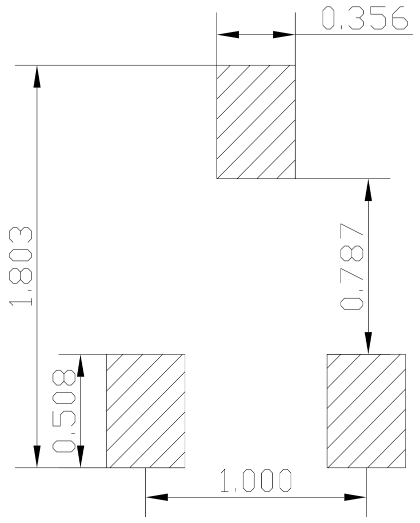
PACKAGE OUTLINE

Plastic surface mounted package SOT-523



SOT-523		
Dim	Min	Max
A	1.5	1.7
B	0.75	0.85
C	0.6	0.8
D	0.15	0.3
G	0.9	1.1
H	0.02	0.1
J	0.1Typical	
K	1.45	1.75
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA2081	SOT-523	3000/Tape&Reel